
Radiation Effects on Electronics

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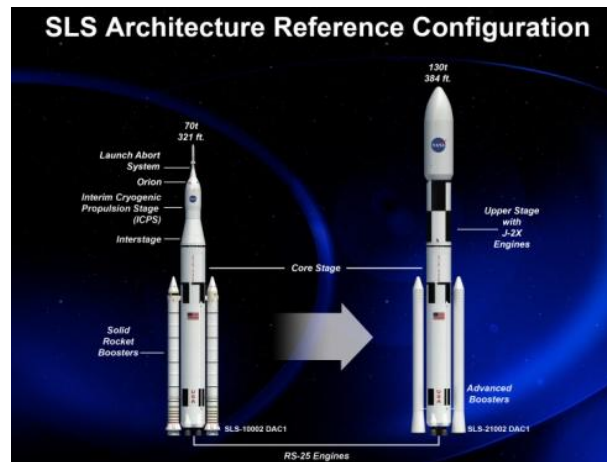


Support the Computing Needs of Space Exploration & Science

- Computation
- Power Efficiency
- Mass



Space Launch System (SLS)

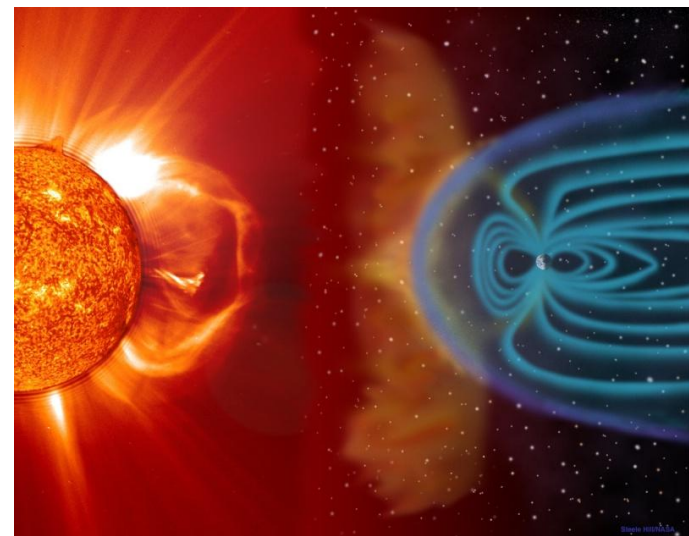


Provide a Radiation Tolerant Platform for Reconfigurable Computing

- Reconfigurable Computing as a means to provide:
 - Increased Computation of Flights Systems
 - Reduced Power of Flight Systems
 - Reduced Mass of Flight Hardware
 - Mission Flexibility through Real-Time Hardware Updates
- Support FPGA-based Reconfigurable Computing through an underlying architecture with inherent radiation tolerance to Single Event Effects



The Future



The Problem



On Earth Our Computers are Protected

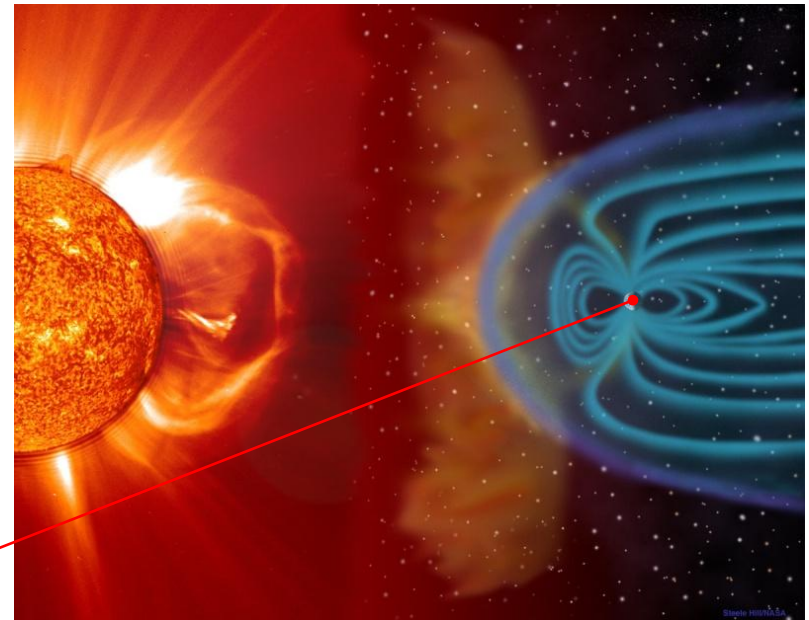
- Our magnetic field deflects the majority of the radiation
- Our atmosphere attenuates the radiation that gets through our magnetic field

Our Satellites Operate In Trapped Radiation in the Van Allen Belts

- High flux of trapped electrons and protons

In Deep Space, Nothing is Protected

- Radiation from our sun
- Radiation from other stars
- Particles & electromagnetic

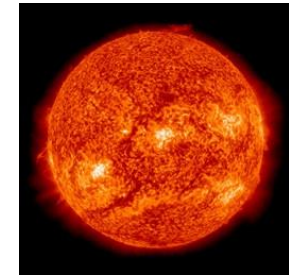


You Are Here



Where Does Space Radiation Come From?

- Nuclear fusion in stars creates light and heavy ions + EM
- Stars consists of an abundant amount of Hydrogen ($^1\text{H} = 1$ Proton) at high temperatures held in place by gravity



1. The strong nuclear force pulls two Hydrogen (^1H) atoms together overcoming the Coulomb force and fuses them into a new nucleus

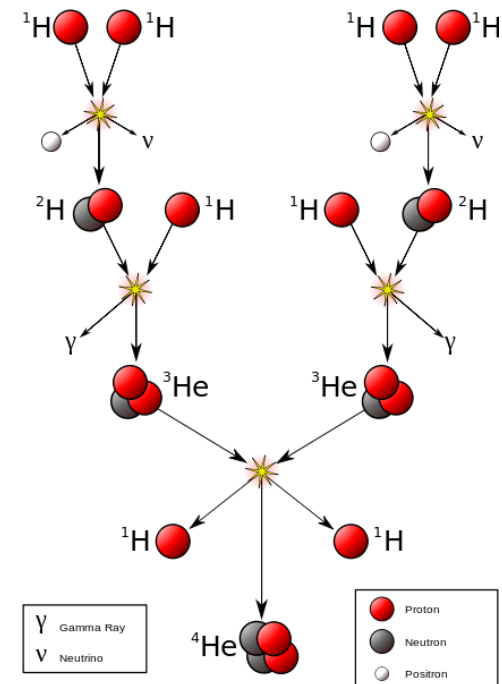
- The new nucleus contains 1 proton + 1 neutron
- This new nucleus is called *Deuterium (D)* or *Heavy Hydrogen (^2H)*
- Energy is given off during this reaction in the form of a Positron and a Neutrino

2. The Deuterium (^2H) then fuses with Hydrogen (^1H) again to form yet another new nucleus

- This new nucleus contains 2 protons + 1 neutron
- This nucleus is called *Tritium* or *Hydrogen-3 (^3H)*
- Energy is given off during this reaction in the form of a Gamma Ray

3. Two Tritium nuclei then fuse to form a Helium nucleus

- The new Helium nucleus (^4H) contains 2 protons + 2 neutrons
- Energy is given off in the form of Hydrogen (e.g., protons)



Radiation Categories

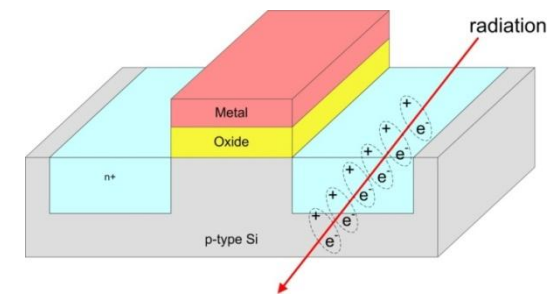
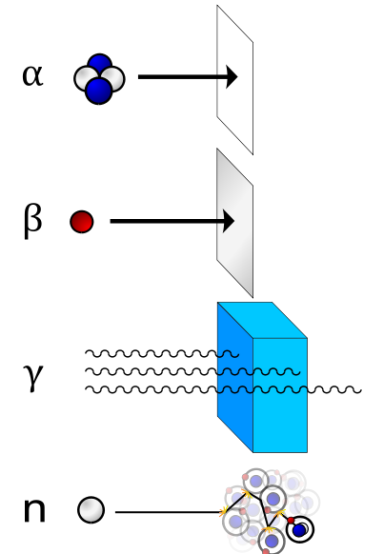
1. Ionizing Radiation
 - Sufficient energy to remove electrons from atomic orbit
 - Ex. High energy photons, charged particles
2. Non-Ionizing Radiation
 - Insufficient energy/charge to remove electrons from atomic orbit
 - Ex., microwaves, radio waves

Types of Ionizing Radiation

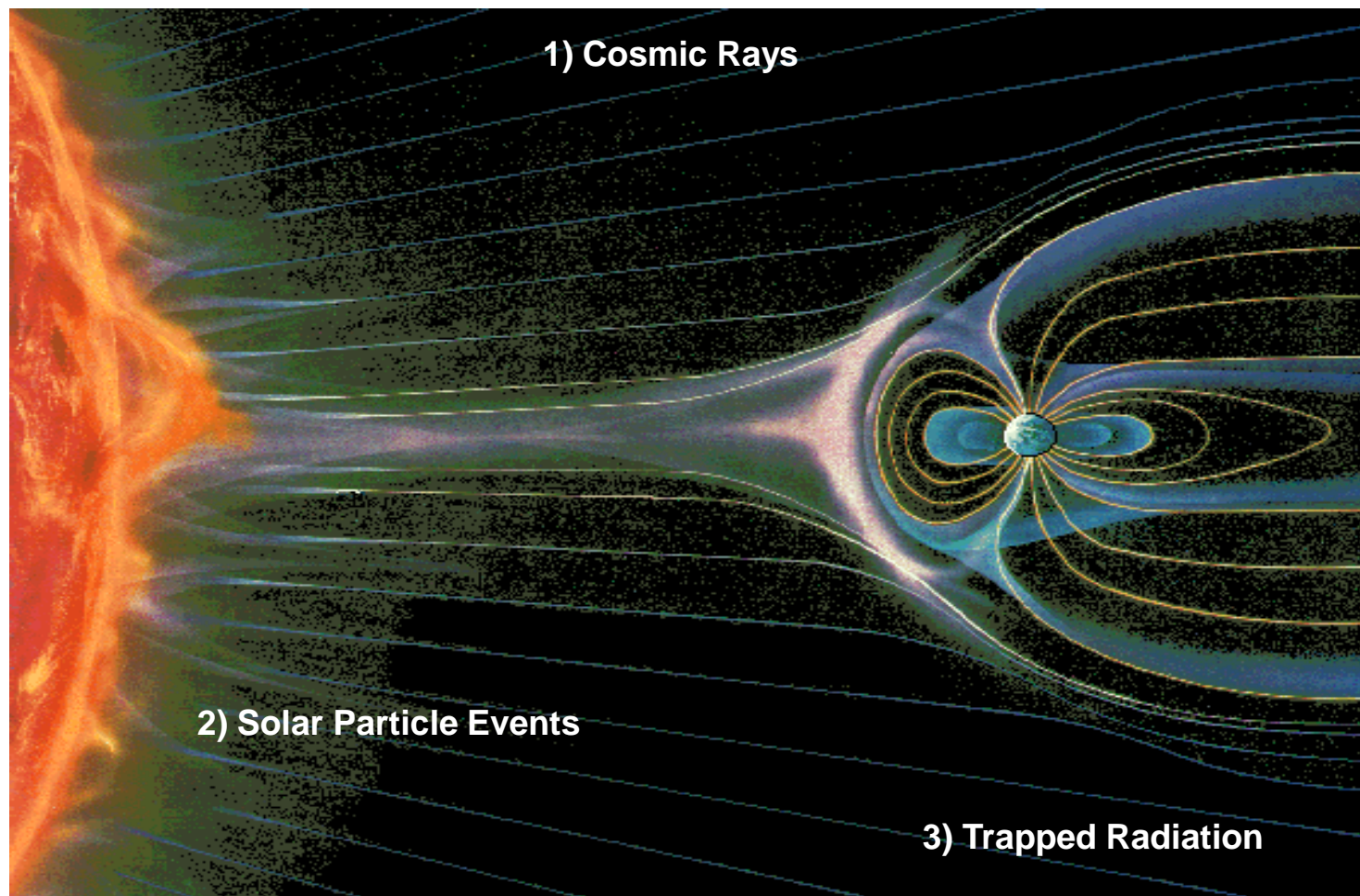
1. Gamma & X-Rays (photons)
 - Sufficient energy in the high end of the UV spectrum
2. Charged Particles
 - Electrons, positrons, protons, alpha, beta, heavy ions
3. Neutrons
 - No electrical charge but ionize indirectly through collisions

What Type are Electronics Sensitive To?

- Ionization which causes electrons to be displaced
- Particles which collide and displace silicon crystal



Classes of Ionizing Space Radiation



Classes of Ionizing Space Radiation

1. Cosmic Rays

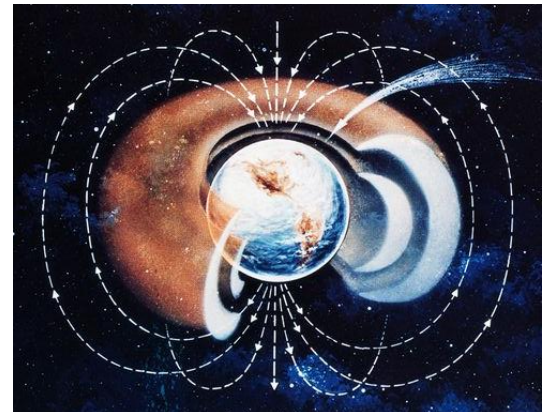
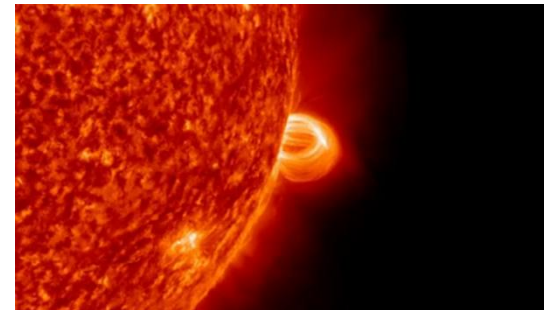
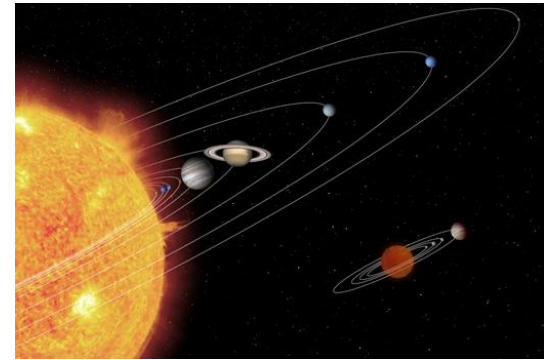
- Originating for our sun (Solar Wind) and outside our solar system (Galactic)
- Mainly Protons and heavier ions
- Low flux

2. Solar Particle Events

- Solar flares & Coronal Mass Ejections
- Electrons, protons, alpha, and heavier ions
- Event activity tracks solar min/max 11 year cycle

3. Trapped Radiation

- Earth's Magnetic Field traps charged particles
- Inner Van Allen Belt holds mainly protons (10-100's of MeV)
- Outer Van Allen Belt holds mainly electrons (up to ~7 MeV)
- Heavy ions also get trapped



Which radiation is of most concern to electronics?

Concern

- Protons (${}^1\text{H}$)
 - Makes up ~85% of galactic radiation
 - Larger Mass than electron (1800x), harder to deflect
- Beta Particles (electrons & positrons)
 - Makes up ~1% of galactic space
 - More penetrating than alphas
- Heavy Ions
 - Makes up <1% of galactic radiation
 - High energy (up to GeV) so shielding is inefficient
- Neutrons
 - Uncharged so difficult to stop

No Concern

- Alpha Particles (He nuclei)
 - Makes up ~14% of galactic radiation
 - ~ 5MeV energy level & highly ionizing but...
 - Low penetrating power (50mm in air, 23um in silicon)
 - Can be stopped by a sheet of paper
- Gamma
 - Highly penetrating but an EM wave
 - Lightly ionizing



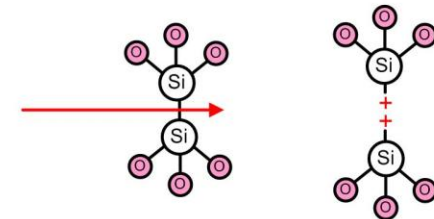
What are the Effects?

1. Total Ionizing Dose (TID)

- Cumulative long term damage due to ionization.
- Primarily due to low energy protons and electrons due to higher, more constant flux, particularly when trapped
- Problem #1 – Oxide Breakdown
 - » Threshold Shifts
 - » Leakage Current
 - » Timing Changes

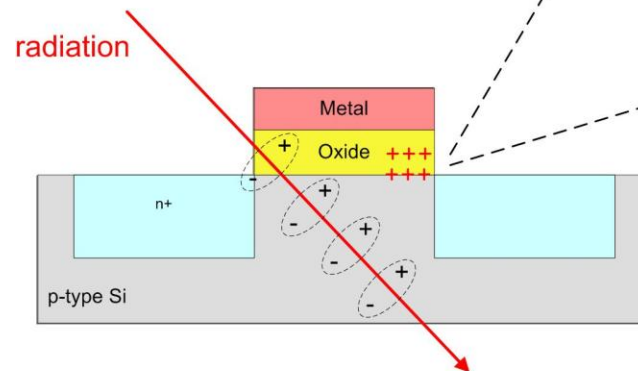
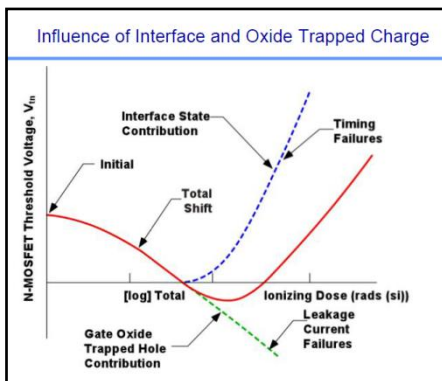
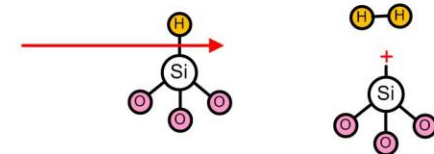
Hole Trapping

- EHP formed by ionization
- Electrons recombine quicker due to faster mobility
- Holes get “stuck” due to lower mobility
- Lowers V_t by effectively “thinning” the oxide
- V_t eventually goes negative turning on MOS



Interface Trapping

- The Si/SiO₂ interface typically contains Si/H bonds
- This is due to the annealing process in hydrogen
- When this bond is severed, H will bond with itself
- This leaves a dangling Si bond with net positive charge
- This initially lowers V_t and then ultimately raises it.



What are the Effects?

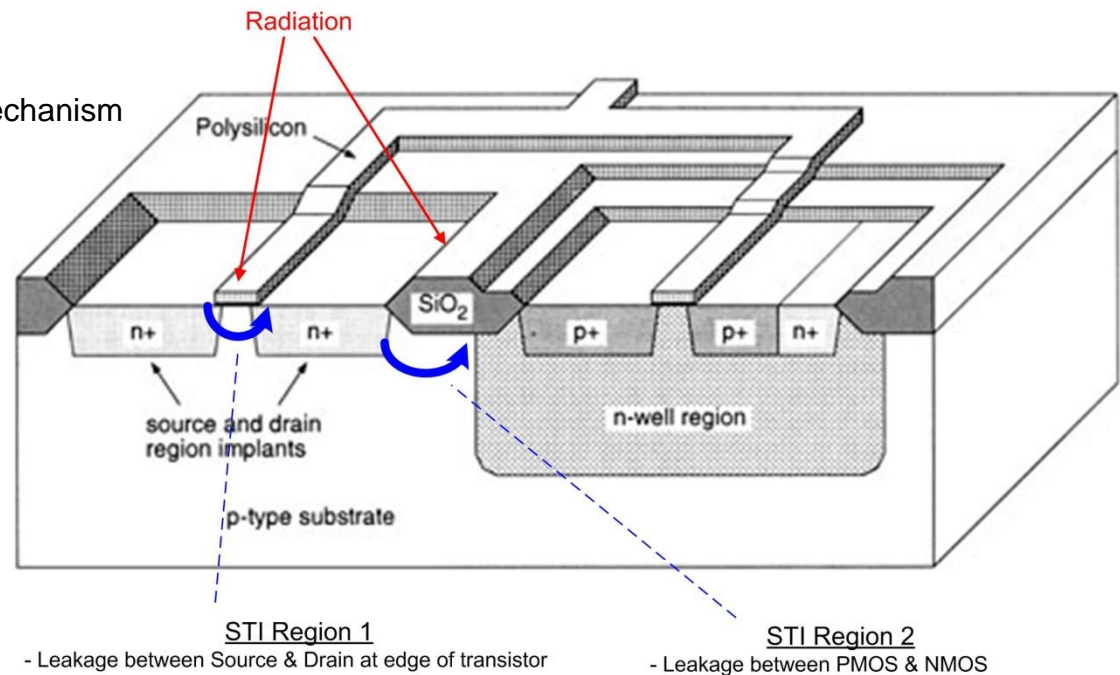
1. Total Ionizing Dose (TID) Cont...

o Problem #2 –Leakage Current

- » Hole trapping slowly “dopes” field oxides to become conductive
- » This is the dominant failure mechanism for commercial processes

Shallow Trench to Thin Oxide Interface (STI)

- Radiation “dopes” the Field Oxide to become conductive and allows current to flow through isolation regions

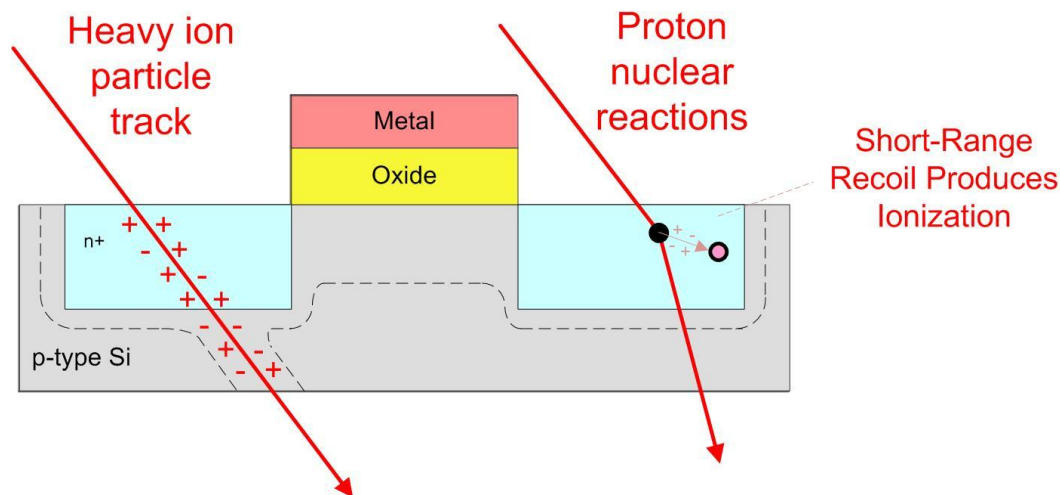


What are the Effects?

2. Single Event Effects (SEE)

- Electron/hole pairs created by a single particle passing through semiconductor
- Primarily due to heavy ions and high energy protons
- Excess charge carriers cause current pulses
- Creates a variety of destructive and non-destructive damage
- The ionization *itself* does not cause damage, the damage is secondary due to parasitic circuits

“Critical Charge” = the amount of charge deposited to change the state of a gate

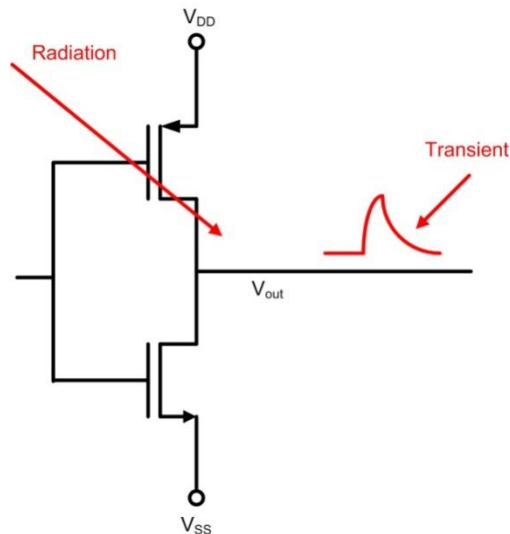


What are the Effects?

2. Single Event Effects (SEE) - **Non-Destructive** (e.g., soft faults)

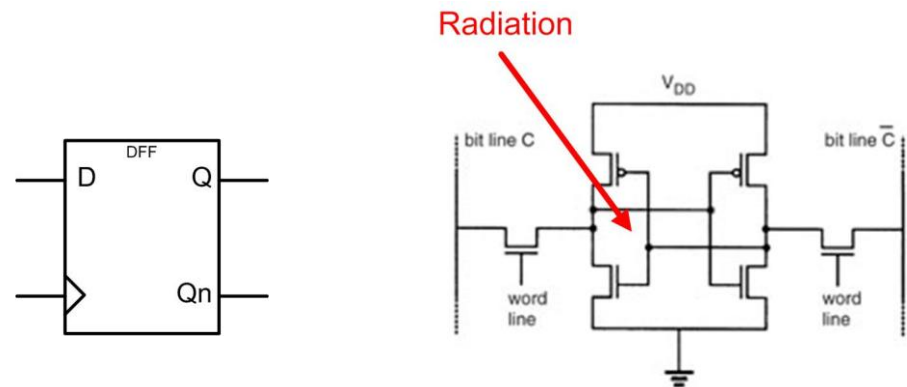
Single Event Transients (SET)

- An induced pulse that can flip a gate
- Temporary glitches in combinational logic



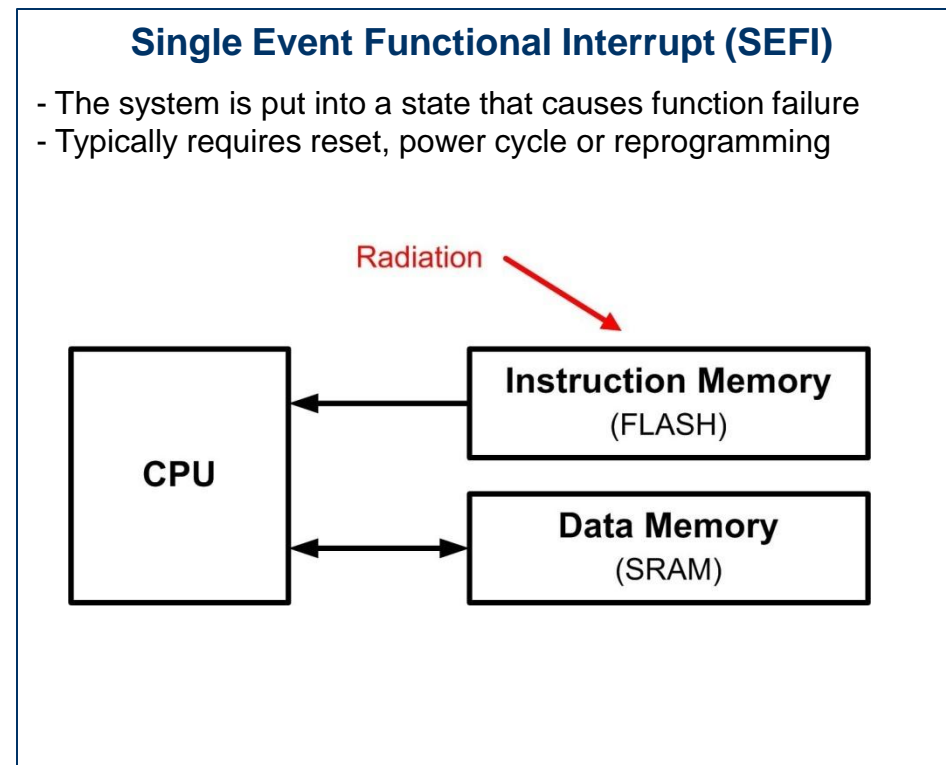
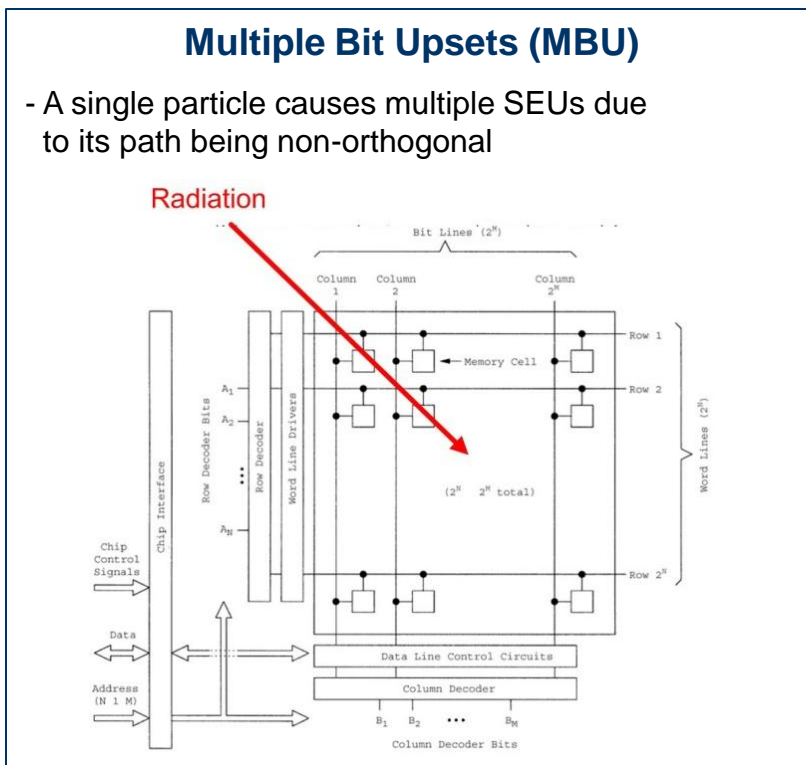
Single Event Upsets (SEU)

- The pulse is captured by a storage device resulting in a state change



What are the Effects?

2. Single Event Effects (SEE) - **Non-Destructive** (e.g., soft faults)

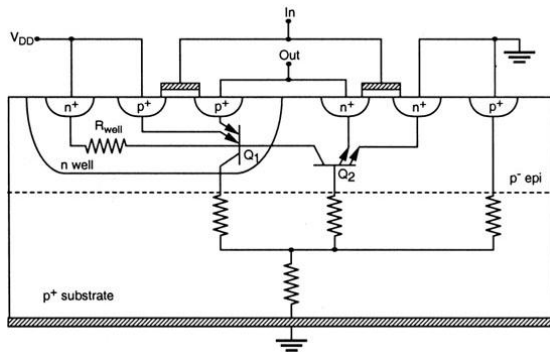


What are the Effects?

2. Single Event Effects (SEE) – **Destructive** (e.g., hard faults)

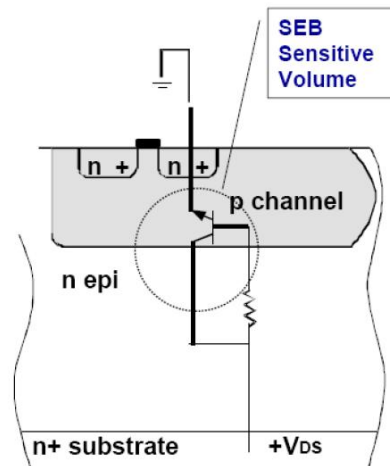
Single Event Latchup (SEL)

- Parasitic NPN/PNP transistors are put into positive feedback condition (PNPN).
- Runaway current damages device
- Due to heavy ions, protons, neutrons.



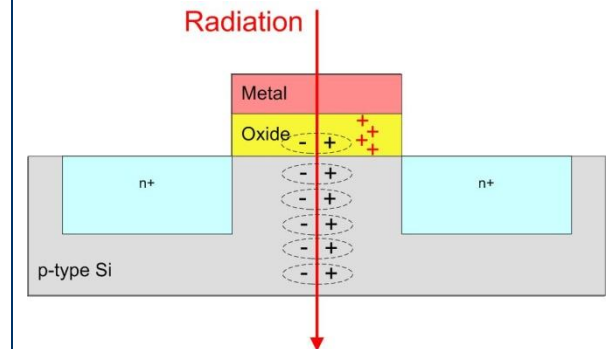
Single Event Burnout (SEB)

- Localized current in body of device turns on parasitic bipolar transistors.
- Runaway current causes heat.
- Due primarily to heavy ions.



Single Event Gate Rupture (SEGR)

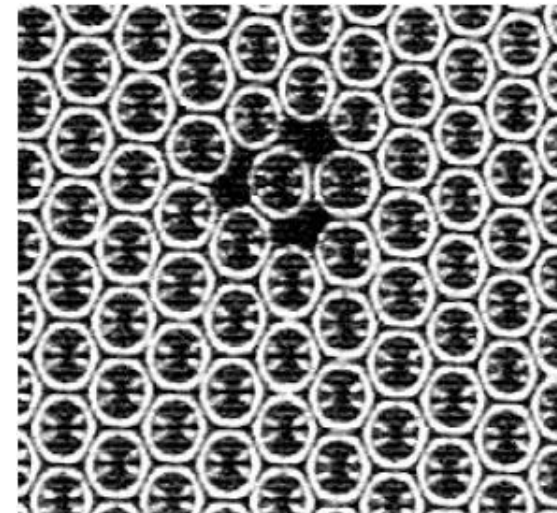
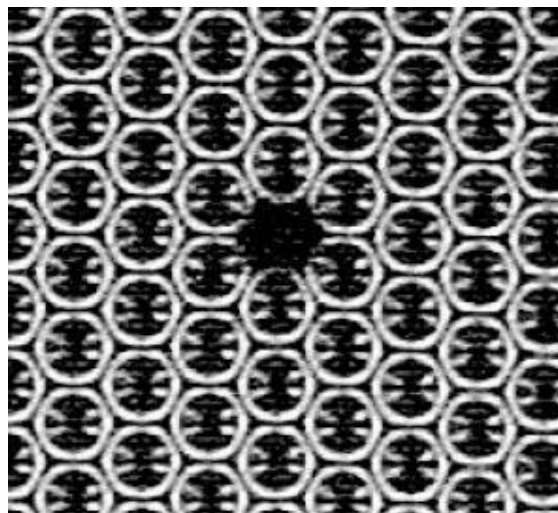
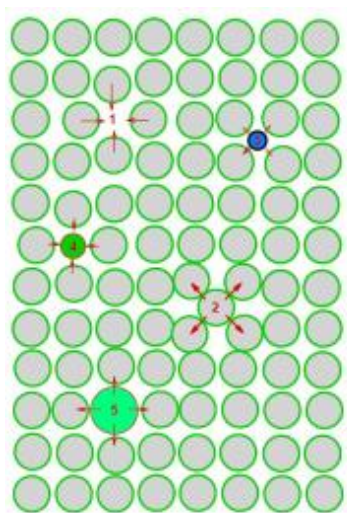
- Permanent short through gate oxide due to hole trapping.
- Thin oxides are especially immune.
- Due to heavy ions.



What are the Effects?

3. Displacement Damage

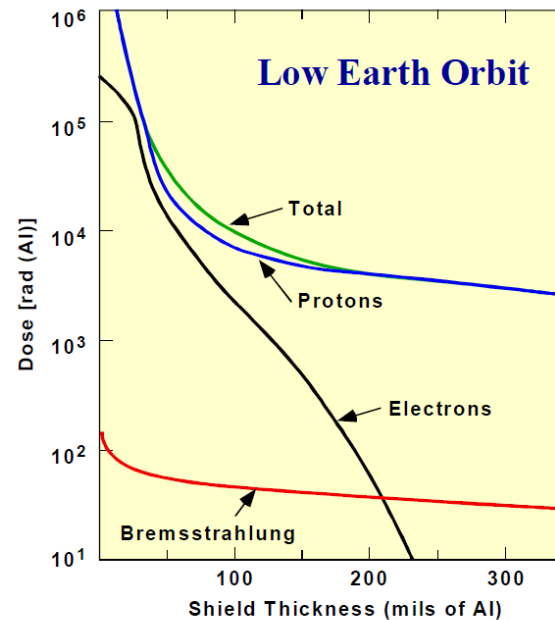
- Cumulative long term damage to protons, electrons, and neutrons
- Not an ionizing effect but rather collision damage
- Minority Carrier Degradation
 - » Reduced gain & switching speed
 - » Particularly damaging for optoelectronic & linear circuits



Shielding

- Shielding helps for protons and electrons $<30\text{MeV}$, but has diminishing returns after $0.25''$.
- This shielding is typically inherent in the satellite/spacecraft design.

Shield Thickness vs. Dose Rate (LEO)



Radiation Hardened by Design (RHBD)

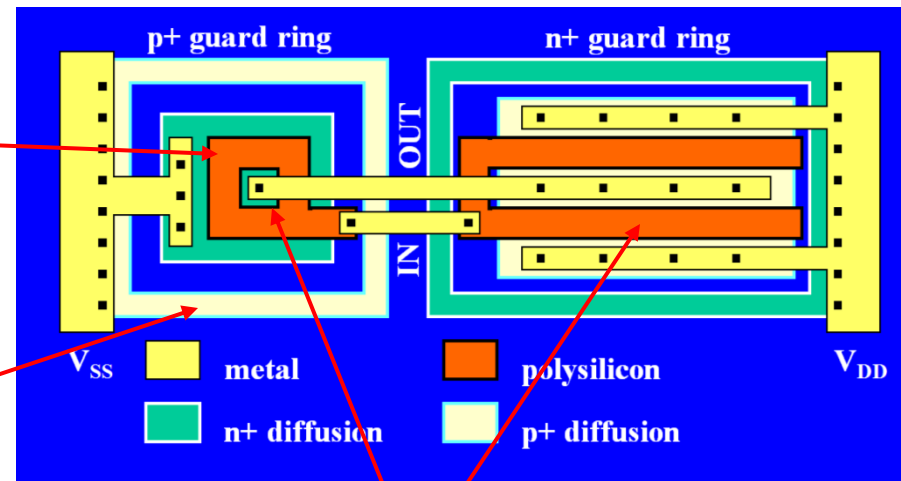
- Uses commercial fabrication process
- Circuit layout techniques are implemented which help mitigate effects

Enclosed Layout Transistors

- Eliminates edge of drain terminal
- This eliminates any leakage current between source & drain due near edge of gate (**STI Region 1**)

Guard Rings

- Reduces leakage between NMOS & PMOS devices due to hole trapping in Field Oxide (**STI Region 2**)
- Separation of device + body contacts
- Adds ~20% increase in area



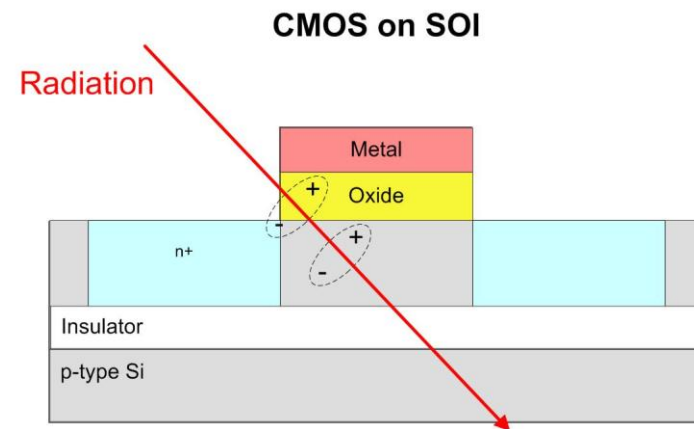
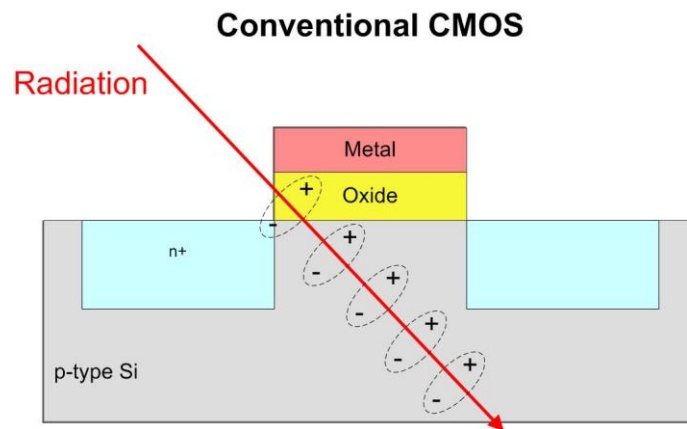
Thin Gate Oxide

- This oxide reduces probability of hole trapping.
- Process nodes $<0.5\mu\text{m}$ typically are immune to V_{gs} shift in the gate.



Radiation Hardened by Process (RHBP)

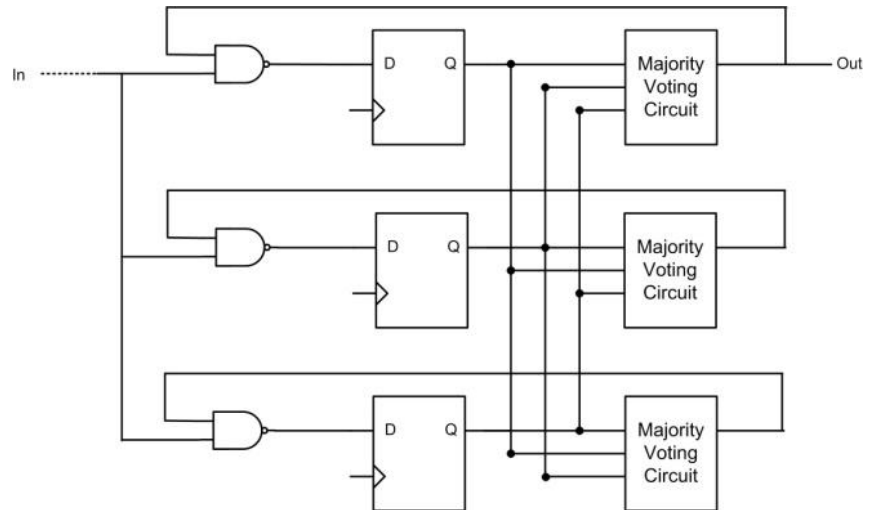
- An insulating layer is used beneath the channels
- This significantly reduces the ion trail length and in turn the electron/hole pairs created
- The bulk can also be doped to be more conductive so as to resist hole trapping



Radiation Tolerance Through Architecture

1. Triple Module Redundancy

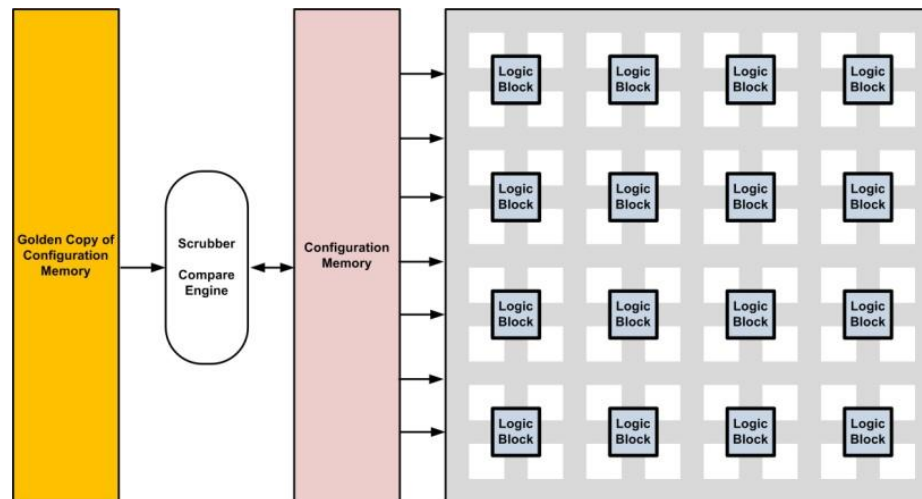
- Triplicate each circuit
- Use a majority voter to produce output
- Advantages
 - » Able to address faults in real-time
 - » Simple
- Disadvantages
 - » Takes >3x the area
 - » Voter needs to be triplicated also to avoid single-point-of-failure
 - » Doesn't handle Multiple-Bit-Upsets



Radiation Tolerance Through Architecture Cont...

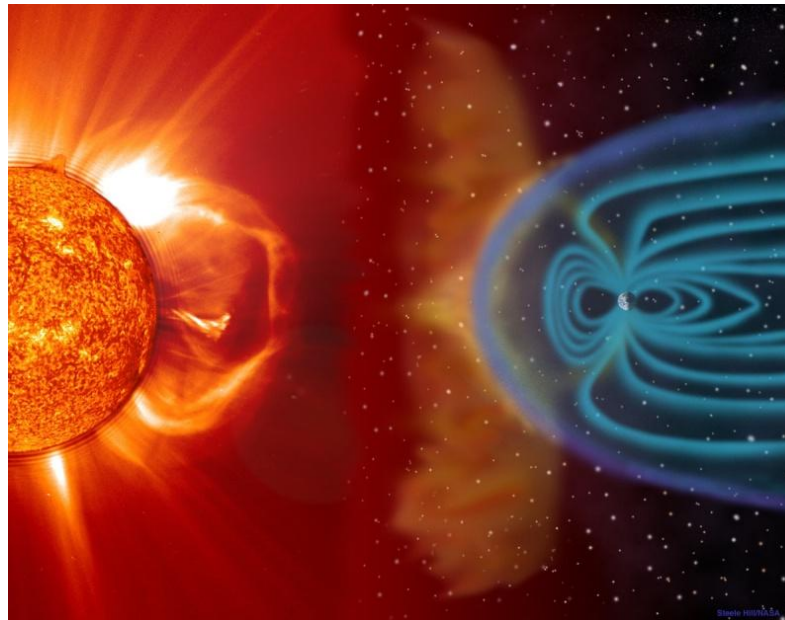
2. Scrubbing

- Compare contents of a memory device to a “Golden Copy”
- Golden Copy is contained in a radiation immune technology (fuse-based memory, MROM, etc...)
- Advantages
 - » Simple & Effective
- Disadvantages
 - » Sequential searching pattern can have latency between fault & repair



Effects Overview

- Primary Concern is Heavy Ions & high energy protons
- All modern computer electronics experience TID and will eventually go out
- Heavy Ions causing SEEs cannot be stopped and an architectural approach is used to handle them.



Questions?

